

DCR820SG

Phase Control Thyristor

Supersedes October 2000 version, DS4214-5.1

DS4214-6.0 July 2001

FEATURES

- Double Side Cooling
- High Surge Capability

APPLICATIONS

- High Power Drives
- High Voltage Power Supplies
- DC Motor Control
- Welding
- Battery Chargers

VOLTAGE RATINGS

Type Number	Repetitive Peak Voltages V _{DRM} V RRM V	Conditions
DCR820SG65	6500	$T_{vi} = 0^{\circ} \text{ to } 125^{\circ}\text{C},$
DCR820SG64	6400	$I_{DRM} = I_{RRM} = 50 \text{mA},$
DCR820SG63	6300	V_{DRM} , V_{RRM} $t_p = 10 ms$,
DCR820SG62	6200	V _{DSM} & V _{RSM} =
DCR820SG61	6100	V _{DRM} & V _{RRM} + 100V
DCR820SG60	6000	Respectively

Lower voltage grades available.

ORDERING INFORMATION

When ordering, select the required part number shown in the Voltage Ratings selection table.

For example:

DCR820SG62

Note: Please use the complete part number when ordering and quote this number in any future correspondance relating to your order.

KEY PARAMETERS

 $\begin{array}{lll} {\rm V_{DRM}} & 6500{\rm V} \\ {\rm I_{T(AV)}} & 387{\rm A} \\ {\rm I_{TSM}} & 6000{\rm A} \\ {\rm dVdt^*} & 1000{\rm V/\mu s} \\ {\rm dI/dt} & 100{\rm A/\mu s} \\ \end{array}$

^{*}Higher dV/dt selections available

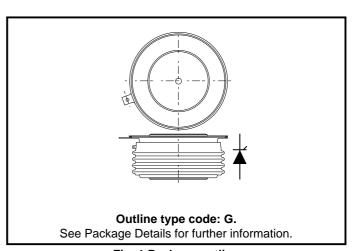


Fig. 1 Package outline



CURRENT RATINGS

T_{case} = 60°C unless stated otherwise

Symbol	Parameter	Conditions	Max.	Units			
Double Sid	Double Side Cooled						
I _{T(AV)}	Mean on-state current	Half wave resistive load	387	А			
I _{T(RMS)}	RMS value	-	608	А			
I _T	Continuous (direct) on-state current	-	567	А			
Single Side	Single Side Cooled (Anode side)						
I _{T(AV)}	Mean on-state current	Half wave resistive load	260	А			
I _{T(RMS)}	RMS value	-	408	А			
I _T	Continuous (direct) on-state current	-	357	А			

CURRENT RATINGS

T_{case} = 80°C unless stated otherwise

Symbol	Parameter	Conditions	Max.	Units			
Double Sid	Double Side Cooled						
I _{T(AV)}	Mean on-state current	Half wave resistive load	310	А			
I _{T(RMS)}	RMS value	-	485	А			
I _T	Continuous (direct) on-state current	-	447	А			
Single Side	Single Side Cooled (Anode side)						
I _{T(AV)}	Mean on-state current	Half wave resistive load	204	А			
I _{T(RMS)}	RMS value	-	321	А			
I _T	Continuous (direct) on-state current	-	279	А			



SURGE RATINGS

Symbol	Parameter	Conditions	Max.	Units
I _{TSM}	Surge (non-repetitive) on-state current	10ms half sine; T _{case} = 125°C	4.8	kA
l ² t	I ² t for fusing	V _R = 50% V _{RRM} - 1/4 sine	115 x 10 ³	A²s
I _{TSM}	Surge (non-repetitive) on-state current	10ms half sine; T _{case} = 125°C	6.0	kA
l ² t	I ² t for fusing	V _R = 0	180 x 10 ³	A²s

THERMAL AND MECHANICAL DATA

Symbol	Parameter	Conditions		Min.	Max.	Units
	Thermal resistance - junction to case	Double side cooled	dc	-	0.032	°C/W
$R_{th(j-c)}$		Single side cooled	Anode dc	-	0.064	°C/W
			Cathode dc	-	0.064	°C/W
В	Thermal resistance - case to heatsink	Clamping force 12.0kN with mounting compound	Double side	-	0.008	°C/W
$R_{th(c-h)}$			Single side	-	0.016	°C/W
$T_{v_{j}}$	Virtual junction temperature	On-state (conducting)		-	135	°C
		Reverse (blocking)		-	125	°C
T _{stg}	Storage temperature range			-55	150	°C
-	Clamping force			10.8	13.2	kN



DYNAMIC CHARACTERISTICS

Symbol	Parameter	Conditions		Min.	Max.	Units
I _{RRM} /I _{DRM}	Peak reverse and off-state current	At V _{RRM} /V _{DRM} , T _{case} = 125°C		-	50	mA
dV/dt	Maximum linear rate of rise of off-state voltage	To 67% V _{DRM} T _j = 125°C.		-	1000	V/µs
117.16		From 67% V _{DRM} to 1000A,	Repetitive 50Hz	-	50	A/μs
dl/dt	Rate of rise of on-state current	Gate source 10V, 5Ω $t_r \le 0.5 \mu s$. $T_j = 125 ^{\circ} C$.	Non-repetitive	-	100	A/μs
V _{T(TO)}	Threshold voltage	At T _{vj} = 125°C		-	1.6	٧
r _T	On-state slope resistance	At T _{vj} = 125°C		-	3.5	mΩ
t _{gd}	Delay time	$V_D = 67\% V_{DRM}$, Gate source 20V, 10Ω Rise time $0.5\mu s$, $T_j = 25^{\circ}C$		-	3.3	μs
IL	Latching current	$T_{j} = 25^{\circ}C, V_{D} = 20V.$		-	1	А
I _H	Holding current	$T_{j} = 25^{\circ}C, V_{D} = 5V, I_{T} = 5A, I_{TM} = 500A$		30	120	mA
t _q	Turn-off time	$I_T = 500A$, $t_p = 1$ ms, $T_j = 125$ °C, $V_{RM} = 100$ V, $dI_{RR}/dt = 10$ A/ μ s, $dV_{DR}/dt = 25$ V/ μ s to 3000V		500	1200	μs
$Q_{_{\rm S}}$	Stored charge - triangular approximation through I _{RR} and 25% I _{RR}	$I_{T} = 320A, -dI_{T}/dt = 6A/\mu s$		600	1500	μС

GATE TRIGGER CHARACTERISTICS AND RATINGS

Symbol	Parameter	Conditions		Max.	Units
V _{GT}	Gate trigger voltage	$V_{DRM} = 5V, T_{case} = 25^{\circ}C$	-	3.0	\ \
I _{GT}	Gate trigger current	$V_{DRM} = 5V$, $T_{case} = 25^{\circ}C$	-	300	mA
$V_{\sf GD}$	Gate non-trigger voltage	At V _{DRM} T _{case} = 125°C	-	0.25	V
V_{FGM}	Peak forward gate voltage	Anode positive with respect to cathode	-	30	V
V _{FGN}	Peak forward gate voltage	Anode negative with respect to cathode	-	0.25	٧
V _{RGM}	Peak reverse gate voltage		-	5	V
I _{FGM}	Peak forward gate current	Anode positive with respect to cathode	-	10	А
P _{GM}	Peak gate power	See Fig.8/9 Gate characteristics curves and table	-	100	W
P _{G(AV)}	Mean gate power		-	5	W



CURVES

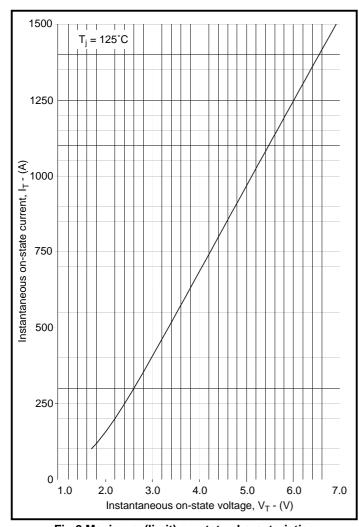


Fig.2 Maximum (limit) on-state characteristics

$$V_{TM}$$
 Equation:-
 $V_{TM} = A + Bln (I_T) + C.I_T + D.\sqrt{I_T}$

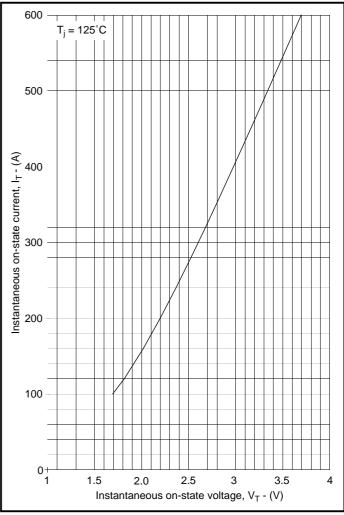
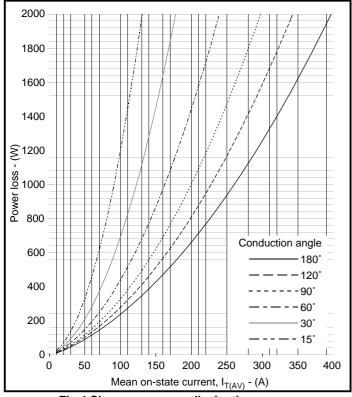


Fig.3 Maximum (limit) on-state characteristics

Where
$$A = -0.759775$$

 $B = 0.639225$
 $C = 0.004376$
 $D = -0.092153$
these values are valid for $T_i = 125^{\circ}C$ for $I_T 100A$ to 1500A

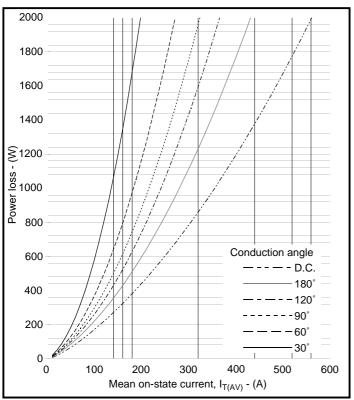




800 700 600 500 Power loss - (W) - 300 300 Conduction angle 200 - -90° **– – 6**0° 100 ·30° - - 15° \bot \bot \bot 100 150 200 250 Mean on-state current, $I_{T(AV)}$ - (A)

Fig.4 Sine wave power dissipation curves

Fig.5 Sine wave power dissipation curves





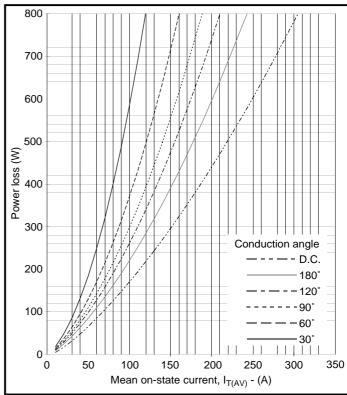


Fig.7 Square wave power dissipation curves



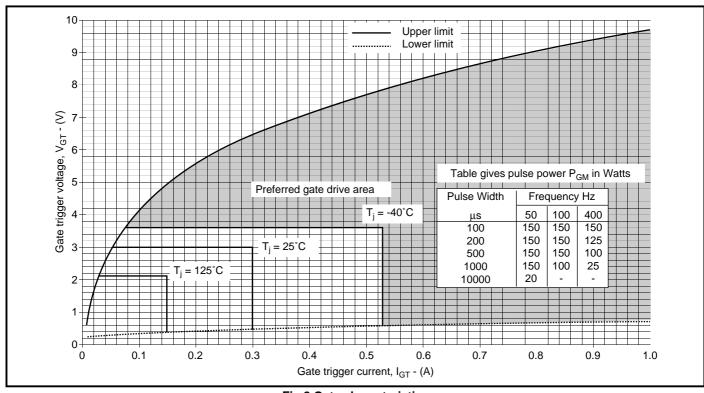


Fig.8 Gate characteristics

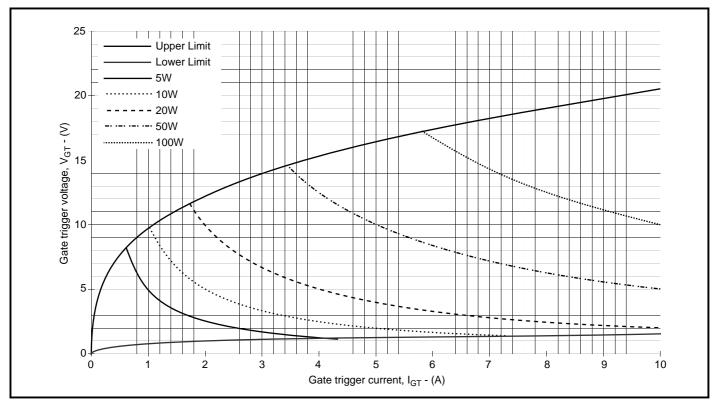
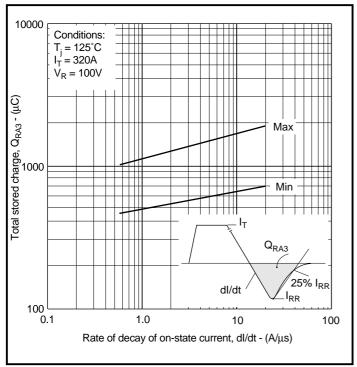


Fig.9 Gate characteristics





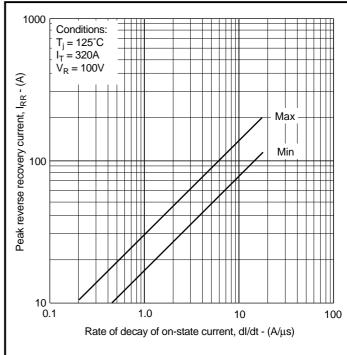


Fig.10 Stored charge

Fig.11 Reverse recovery current

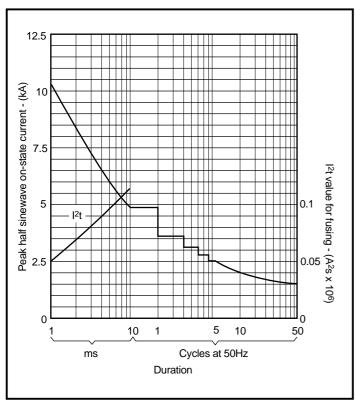


Fig.12 Surge (non-repetitive) on-state current vs time (with 50% V_{RRM} @ T_{case} = 125°C)

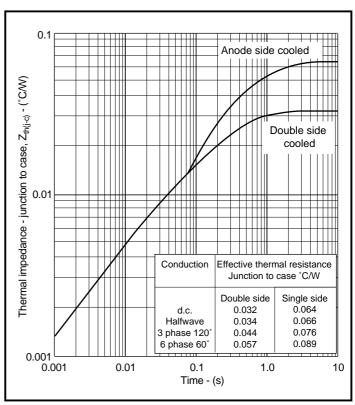
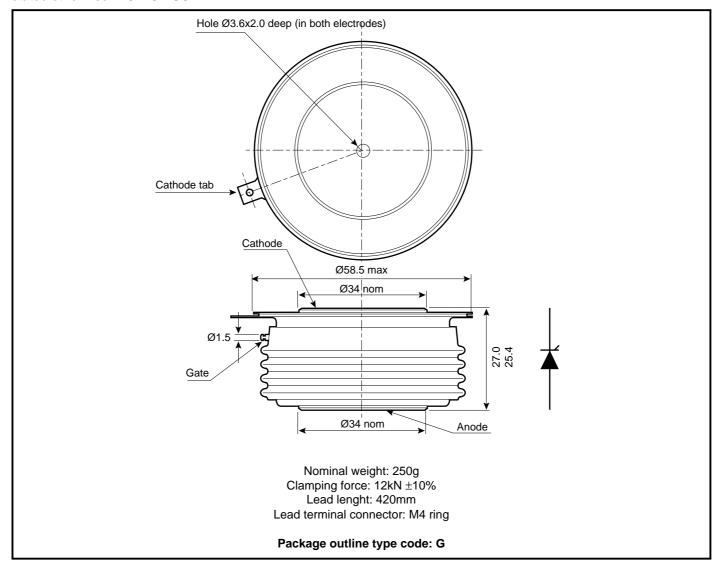


Fig.13 Maximum (limit) transient thermal impedance - junction to case



PACKAGE DETAILS

For further package information, please contact your nearest Customer Service Centre. All dimensions in mm, unless stated otherwise. DO NOT SCALE.





POWER ASSEMBLY CAPABILITY

The Power Assembly group was set up to provide a support service for those customers requiring more than the basic semiconductor, and has developed a flexible range of heatsink / clamping systems in line with advances in device types and the voltage and current capability of our semiconductors.

We offer an extensive range of air and liquid cooled assemblies covering the full range of circuit designs in general use today. The Assembly group continues to offer high quality engineering support dedicated to designing new units to satisfy the growing needs of our customers.

Using the up to date CAD methods our team of design and applications engineers aim to provide the Power Assembly Complete solution (PACs).

DEVICE CLAMPS

Disc devices require the correct clamping force to ensure their safe operation. The PACs range offers a varied selection of pre-loaded clamps to suit all of our manufactured devices. This include cube clamps for single side cooling of 'T' 22mm

Clamps are available for single or double side cooling, with high insulation versions for high voltage assemblies.

Please refer to our application note on device clamping, AN4839

HEATSINKS

Power Assembly has its own proprietary range of extruded aluminium heatsinks. They have been designed to optimise the performance or our semiconductors. Data with respect to air natural, forced air and liquid cooling (with flow rates) is available on request.

For further information on device clamps, heatsinks and assemblies, please contact your nearest Sales Representative or Customer Services.



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